

FLASH MEMORY AND METHOD THEREOF

Abstract

A substrate having a P type shallow doped region is provided, and at least a stacked gate structure having a tunneling oxide, a floating gate, an ONO layer, and a control gate from bottom to top are respectively formed thereon. Then, a P type deep doped region is formed in the substrate alongside the stacked gate structure. Following that, an oxidization process is performed to oxidize the floating gate and the control gate such that an insulating barrier layer is formed. Finally, a drain and a source are formed in the substrate.